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June 23, 2003

MAIL STOP PATENT APPLICATION

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Re:

Application of KIYOKU, Hiroyuki, NAKAMURA, Shuji, KOZAKI, Tokuya,

IWASA, Naruhito, CHOCHO, Kazuyuki

NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE

SEMICONDUCTOR SUBSTRATE, AND NITRIDE SEMICONDUCTOR

DEVICE

Assignee: NICHIA CHEMICAL INDUSTRIES, LTD.

Our Ref: 076117

Dear Sir:

This is a request for a Divisional Application of pending prior Application No. 10/261,487 (Confirmation No. 2874) filed October 2, 2002 of KIYOKU, Hiroyuki, NAKAMURA, Shuji, KOZAKI, Tokuya, IWASA, Naruhito, CHOCHO, Kazuyuki entitled NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE SEMICONDUCTOR SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE.

This application is being filed under 37 C.F.R. § 1.53(b). Enclosed is a specification, including the claims and abstract, 8 sheets of drawings, and a copy of the Declaration and Assignment as filed in the parent application. Also enclosed are a Preliminary Amendment and an Information Disclosure Statement with forms PTO 1449 and PTO/SB/08 A & B (modified; four sheets) listing references cited by applicant and/or the examiner during prosecution of the prior application.

This is a divisional of Application No. 10/261,487 filed October 2, 2002, which is a divisional of Application No. 09/986,332 (pending) filed November 8, 2001, which is a Continuation of application Serial No. 09/603,437 (abandoned) filed June 23, 2000, which is a Division of application Serial No. 09/202,141 filed December 9, 1998, now U.S. Patent 6,153,010, which is a 35 U.S.C. § 371 of PCT/JP98/01640 filed April 9, 1998, the entire contents of which are hereby incorporated by reference.

The prior application is assigned to Group Art Unit 2822.

Priority is claimed from:

Country	Application No	Filing Date
Japan	9-093315	April 11, 1997
Japan	9-174494	June 30, 1997
Japan	9-181071	July 7, 1997





Commissioner for Patents
Divisional of Application No. 10/261,487
June 23, 2003
Page 2

Japan		9-201477	July 28, 1997
Japan		9-277448	October 9, 1997
Japan	÷ .	9-290098	October 22, 1997
Japan		9-324997	November 26, 1997

The priority documents were filed on April 9, 1998, in parent Application No. PCT/JP98/01640. Translations are already of record.

The Government filing fee is calculated as follows:

Total claims	27 -	20	=	7	X	\$18.00	=	\$126.00
Independent claims	2 -	3	=		X	\$84.00	=	\$.00
Base Fee			***************************************					\$750.00

TOTAL FILING FEE

\$876.00

A check for the statutory fee of \$876.00 is attached. The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account. A duplicate copy of this transmittal letter is attached.

The application is timely filed.

Respectfully submitted,

SUGHRUE MION, PLLC Attorneys for Applicant

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WASHINGTON OFFICE

23373

PATENT TRADEMARK OFFICE

Peter D. Olexy

Registration No. 24,513

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q76117

KIYOKU, Hiroyuki, et al.

This is a Divisional Application of

Appln. No.: 10/261,487

Confirmation No.: Unknown

Prior Group Art Unit: 2822

Filed: June 23, 2003

Prior Examiner: Stephen D. Meier

For: NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE SEMICONDUCTOR

SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE

SUBMISSION OF DRAWINGS

MAIL STOP ISSUE FEE

ATTN: OFFICIAL DRAFTSPERSON

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Submitted herewith please find 8 sheets of drawings believed to be in compliance with 37 C.F.R. § 1.84. The Examiner is respectfully requested to acknowledge receipt of these drawings.

Respectfully submitted,

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Date: June 23, 2003